

Silicon Carbide Technology
Development and Device Prototyping

SiC Services

Custom-Tailored SiC Services with One-Stop Solutions from Material to System

4H-SiC is the ideal semiconductor for the realization of high-voltage and high-power electron devices due to its outstanding material properties. With SiC services as a cross-cutting topic of the departments of Fraunhofer IISB and in close collaboration with the in-house brand π -Fab, we offer R&D services ranging from **material development** and **prototype devices** to **module assembly** and **mechatronic systems**.

Our Core Competences

- Simulation and modeling
- Homoepitaxy and defect engineering
- Advanced device concepts and realization
- Customised device and circuit design
- Integrated manufacturing of power devices
- Wafer thinning and packaging
- Device characterization